HOLTEK

HT82V739

1200mW Audio Power Amp with Shutdown

Features

- Operating voltage: 2.2V to 5.5V
- High signal-to-noise ratio
- Low distortion
- Large output voltage swing
- Low power consumption
- Output power 1200mW at 10% THD+N into 8Ω (V_{DD}=5V)
- Wide temperature operating range
- Low power-on and chip enable or disable POP noise.
- Low standby current
- Power off control
- Direct drive speaker
- 8-pin DIP/SOP package

Applications

- Applied for HT36 series, HT86 series and other Holtek products

General Description

HT82V739 is an integrated class AB mono speaker driver contained in a 8-pin DIP/SOP package. The HT82V739 is capable of delivering 1200mW output power to an 8Ω load with less than 10% (THD+N) from a 5V power supply. The very low standby current in shutdown mode contributes to the reduction of power consumption of battery-powered equipments.

Block Diagram

Pin Assignment

HT82V739
8 DIP-A/SOP-A
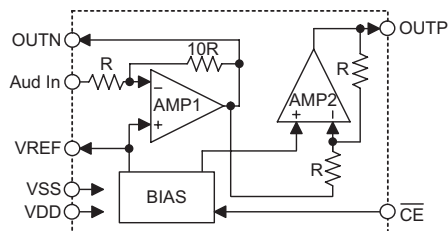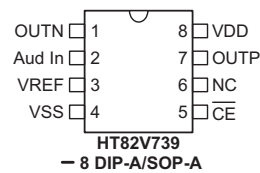
Pin Description

Pin No.	Pin Name	I/O	Description
1	OUTN	O	Negative output
2	Aud In	I	Audio input
3	VREF	O	Speaker non-inverting input voltage reference
4	VSS	—	Negative power supply, ground
5	$\overline{CE}$	I	Chip enable, low active
6	NC	—	Not connected
7	OUTP	O	Positive output
8	VDD	—	Positive power supply

Absolute Maximum Ratings

Supply Voltage ....V_{SS}–0.3V to V_{SS}+6.0V

Input Voltage.............................V_{SS}–0.3V to V_{DD}+0.3V

Storage Temperature ....–50°C to 125°C

Operating Temperature...........................–40°C to 85°C

Note: These are stress ratings only. Stresses exceeding the range specified under ″Absolute Maximum Ratings″ may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

Electrical Characteristics

V_{SS}=0V, Ta=25°C

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
		V_{DD}	Conditions				
D.C. Characteristics							
V_{DD}	Supply Voltage	—	—	2.2	5.0	5.5	V
I_{DD}	Quiescent Power Supply Current	3V	V_{IN}=0V_{P-P}, No load	—	2.2	4.0	mA
		5V		—	3.5	6.0	mA
I_{SD}	Shutdown Power Supply Current	5V	V_{IN}=0V_{P-P}, $\overline{CE}$=V_{DD}, No load	—	—	1	μA
V_{IH}	Input High Voltage for $\overline{CE}$	—	—	0.7V_{DD}	—	V_{DD}	V
V_{IL}	Input Low Voltage for $\overline{CE}$	—	—	0	—	0.3V_{DD}	V
P_O	Output Power	3V	(THD+N)/S≤1%, V_{IN}=1kHz sinewave, R_L=4Ω	198	330	—	mW
			(THD+N)/S≤1%, V_{IN}=1kHz sinewave, R_L=8Ω	180	300	—	
			(THD+N)/S≤1%, V_{IN}=1kHz sinewave, R_L=16Ω	144	240	—	
			(THD+N)/S≤10%, V_{IN}=1kHz sinewave, R_L=4Ω	270	450	—	
			(THD+N)/S≤10%, V_{IN}=1kHz sinewave, R_L=8Ω	240	400	—	
			(THD+N)/S≤10%, V_{IN}=1kHz sinewave, R_L=16Ω	168	280	—	
		5V	(THD+N)/S≤1%, V_{IN}=1kHz sinewave, R_L=4Ω	690	1150	—	mW
			(THD+N)/S≤1%, V_{IN}=1kHz sinewave, R_L=8Ω	570	950	—	
			(THD+N)/S≤1%, V_{IN}=1kHz sinewave, R_L=16Ω	390	650	—	
			(THD+N)/S≤10%, V_{IN}=1kHz sinewave, R_L=4Ω	840	1400	—	
			(THD+N)/S≤10%, V_{IN}=1kHz sinewave, R_L=8Ω	720	1200	—	
			(THD+N)/S≤10%, V_{IN}=1kHz sinewave, R_L=16Ω	480	800	—	
A.C. Characteristics							
t_{ON}	Enable Time	3V	V_{IN}=1kHz sinewave, No load	—	145	—	μs
		5V		—	105	—	μs
(THD+N)/S	Total Harmonic Distortion Plus Noise-to-signal Ratio	5V	Power output=500mW, V_{IN}=1kHz sinewave, R_L=4Ω	—	0.3	—	%
			Power output=500mW, V_{IN}=1kHz sinewave, R_L=8Ω	—	0.18	—	%
			Power output=500mW, V_{IN}=1kHz sinewave, R_L=16Ω	—	0.13	—	%
S/N	Signal to Noise Ratio	5V	V_{IN}=1Vrms 1kHz sinewave, R_L=4Ω	—	66	—	dB
			V_{IN}=1Vrms 1kHz sinewave, R_L=8Ω	—	70	—	dB
			V_{IN}=1Vrms 1kHz sinewave, R_L=16Ω	—	72	—	dB

Functional Description

OUTP Rising Time (t_R)

When $\overline{CE}$ is active low, the HT82V739 needs rising time to output fully on OUTP pin. However, the rising time depends on C1. (*see the application circuits)
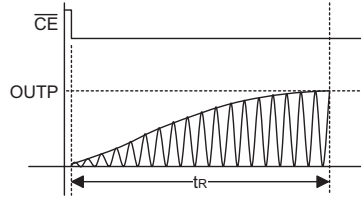

	Capacitor t_R Voltage	0.1μF	1μF	4.7μF	10μF
2.2V		15ms	30ms	90ms	185ms
3V		15ms	30ms	90ms	185ms
4V		15ms	30ms	90ms	185ms

For battery based applications, power consumption is a key issue, therefore the amplifier should be turned off when in the standby state. In order to eliminate any speaker sound bursts while turning the amplifier on, the application circuit, which will incorporate a capacitance value of C1, should be adjusted in accordance with the speaker's audio frequency response. A greater value of C1 will improve the noise burst while turning on the amplifier. The recommended operation sequence is:

Turn On: "Aud In" signal standby (1/2 VDD) → enable amplifier → wait t_R for amplifier ready → "Aud In" signal start

Turn Off: "Aud In" signal finish → disable amplifier → wait t_R for amplifier off → "Aud In" signal off
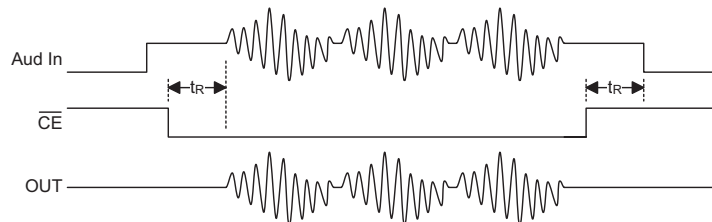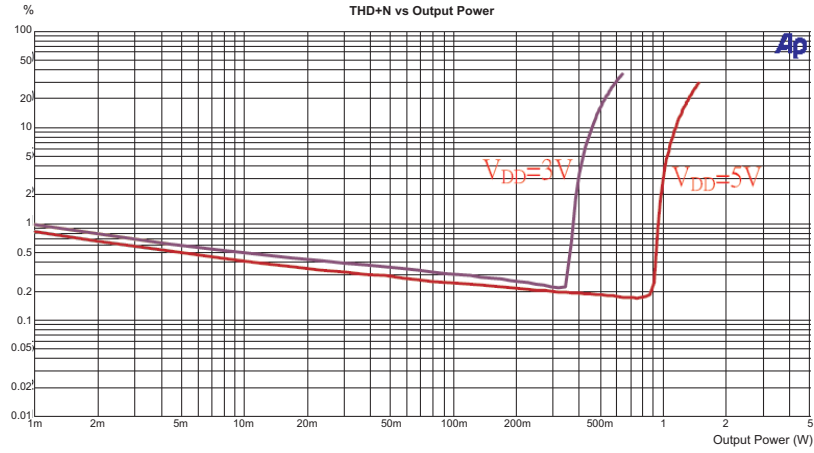

If the application is not powered by batteries and there is no problem with amplifier On/Off issue, a capacitor value of 0.1μF for C1 is recommended.
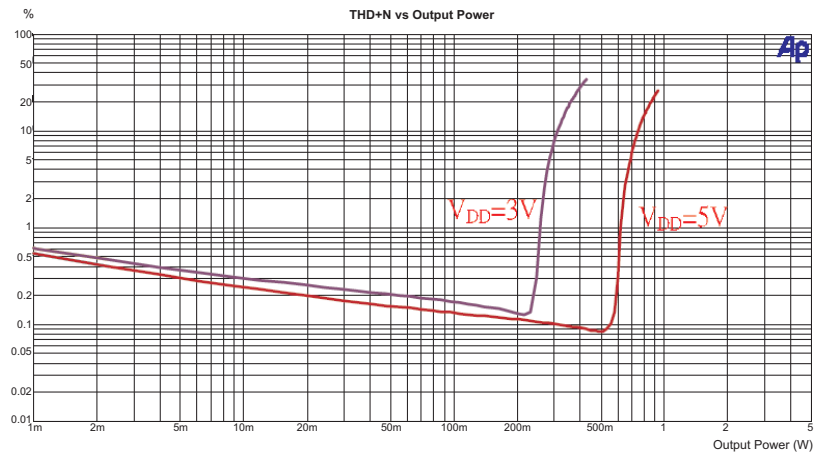
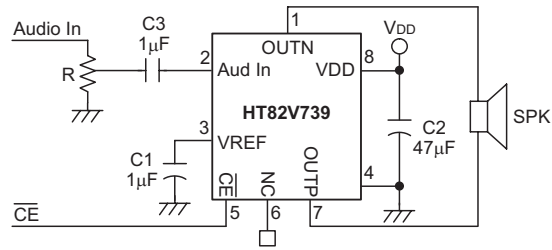**THD+N VS. Output Power**

- $R_{LOAD}=4\Omega$, $V_{IN}=1kHz$ sinewave
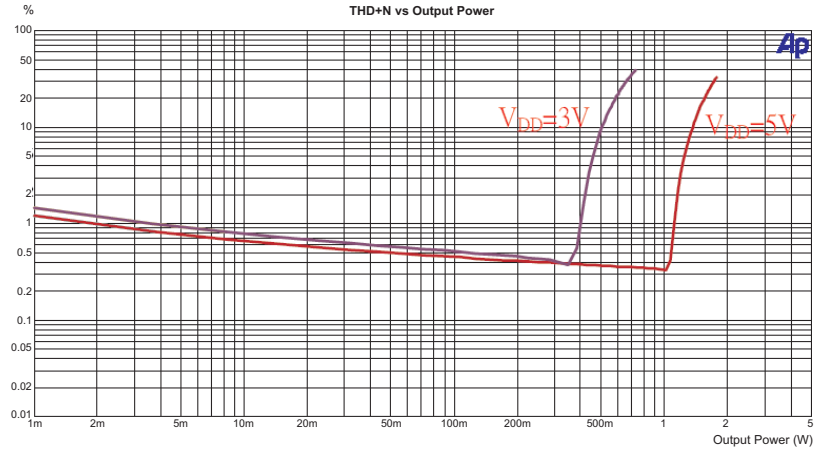
- $R_{LOAD}=8\Omega$, $V_{IN}=1kHz$ sinewave

- $R_{LOAD}=16\Omega$, $V_{IN}=1kHz$ sinewave

Application Circuits
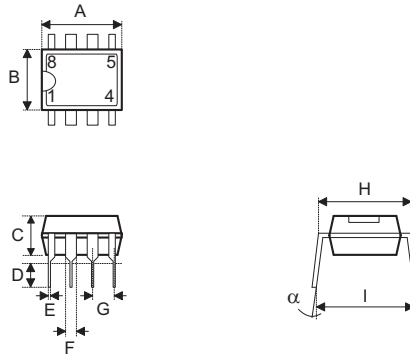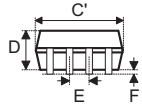
Package Information

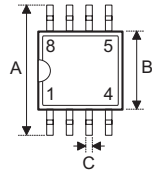**8-pin DIP (300mil) Outline Dimensions**

Symbol	Dimensions in mil		
	Min.	**Nom.**	**Max.**
A	355	—	375
B	240	—	260
C	125	—	135
D	125	—	145
E	16	—	20
F	50	—	70
G	—	100	—
H	295	—	315
I	335	—	375
α	0°	—	15°

8-pin SOP (150mil) Outline Dimensions

Symbol	Dimensions in mil		
	Min.	**Nom.**	**Max.**
A	228	—	244
B	149	—	157
C	14	—	20
C′	189	—	197
D	53	—	69
E	—	50	—
F	4	—	10
G	22	—	28
H	4	—	12
α	0°	—	10°

Product Tape and Reel Specifications

Reel Dimensions
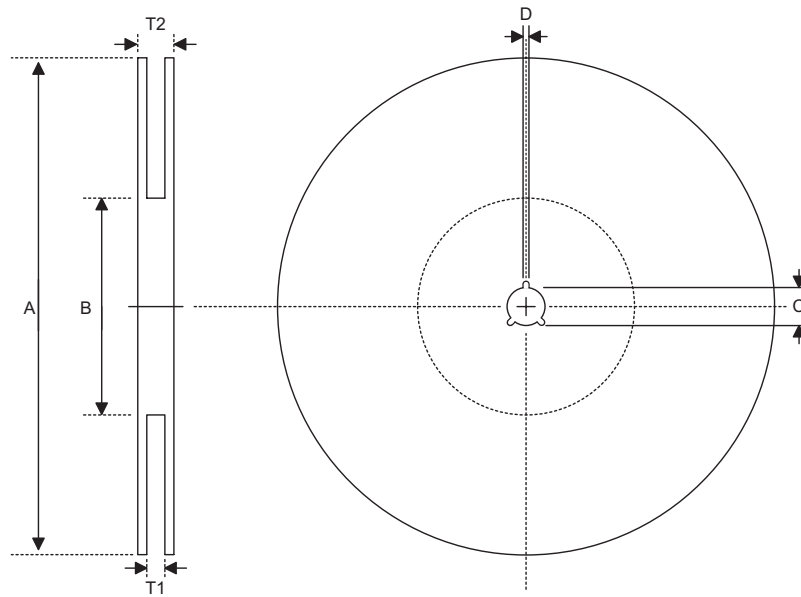
SOP 8N

Symbol	Description	Dimensions in mm
A	Reel Outer Diameter	330±1.0
B	Reel Inner Diameter	62±1.5
C	Spindle Hole Diameter	13.0+0.5 −0.2
D	Key Slit Width	2.0±0.15
T1	Space Between Flange	12.8+0.3 −0.2
T2	Reel Thickness	18.2±0.2

Carrier Tape Dimensions
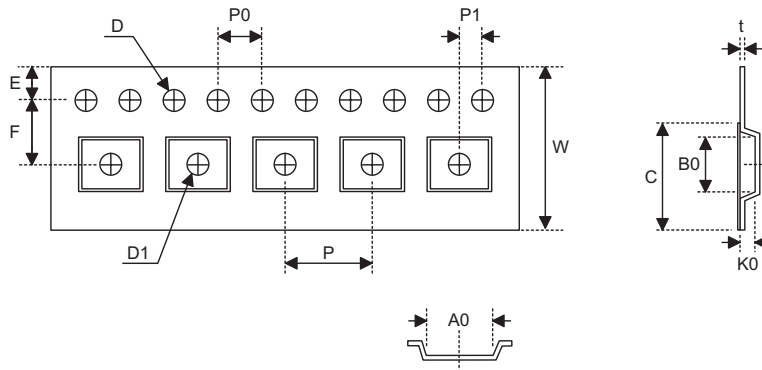
SOP 8N

Symbol	Description	Dimensions in mm
W	Carrier Tape Width	12.0+0.3 −0.1
P	Cavity Pitch	8.0±0.1
E	Perforation Position	1.75±0.1
F	Cavity to Perforation (Width Direction)	5.5±0.1
D	Perforation Diameter	1.55±0.1
D1	Cavity Hole Diameter	1.5+0.25
P0	Perforation Pitch	4.0±0.1
P1	Cavity to Perforation (Length Direction)	2.0±0.1
A0	Cavity Length	6.4±0.1
B0	Cavity Width	5.20±0.1
K0	Cavity Depth	2.1±0.1
t	Carrier Tape Thickness	0.3±0.05
C	Cover Tape Width	9.3

Holtek Semiconductor Inc. (Headquarters)
No.3, Creation Rd. II, Science Park, Hsinchu, Taiwan
Tel: 886-3-563-1999
Fax: 886-3-563-1189
http://www.holtek.com.tw

Holtek Semiconductor Inc. (Taipei Sales Office)
4F-2, No. 3-2, YuanQu St., Nankang Software Park, Taipei 115, Taiwan
Tel: 886-2-2655-7070
Fax: 886-2-2655-7373
Fax: 886-2-2655-7383 (International sales hotline)

Holtek Semiconductor Inc. (Shanghai Sales Office)
7th Floor, Building 2, No.889, Yi Shan Rd., Shanghai, China 200233
Tel: 86-21-6485-5560
Fax: 86-21-6485-0313
http://www.holtek.com.cn

Holtek Semiconductor Inc. (Shenzhen Sales Office)
5/F, Unit A, Productivity Building, Cross of Science M 3rd Road and Gaoxin M 2nd Road, Science Park, Nanshan District,
Shenzhen, China 518057
Tel: 86-755-8616-9908, 86-755-8616-9308
Fax: 86-755-8616-9722

Holtek Semiconductor Inc. (Beijing Sales Office)
Suite 1721, Jinyu Tower, A129 West Xuan Wu Men Street, Xicheng District, Beijing, China 100031
Tel: 86-10-6641-0030, 86-10-6641-7751, 86-10-6641-7752
Fax: 86-10-6641-0125

Holtek Semiconductor Inc. (Chengdu Sales Office)
709, Building 3, Champagne Plaza, No.97 Dongda Street, Chengdu, Sichuan, China 610016
Tel: 86-28-6653-6590
Fax: 86-28-6653-6591

Holtek Semiconductor (USA), Inc. (North America Sales Office)
46729 Fremont Blvd., Fremont, CA 94538
Tel: 1-510-252-9880
Fax: 1-510-252-9885
http://www.holtek.com